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OGOSH46USA

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: )  
Kazutoshi Kojima et al. ) Examiner:  
Application No.: ) Group Art Unit:  
Corresponding International Filing No.: )  
PCT/JP2004/011894 )  
Filed: Herewith )  
For: SILICON CARBIDE EPITAXIAL )  
WAFER, METHOD FOR )  
PRODUCING SUCH WAFER, )  
AND SEMICONDUCTOR )  
DEVICE FORMED ON SUCH )  
WAFER )

Mail Stop PCT  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**SECOND PRELIMINARY AMENDMENT**

Sir:

Please amend the above-identified patent application as follows.

**Amendments to the Specification** begin on page two of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page four of this paper.

**Remarks** begin on page six of this paper.